



WANSEMI  
万尚半导体

WX014P02S3

# Enhancement Mode P-Channel Power MOSFET

SOT23-3/PMOS/-20V/ $\pm$ 12V/-0.7V/-6A/15m $\Omega$

Rev1.0



## -20V, 15mΩ, -6A, P-Channel MOSFET

### 1. Features

- ◆ Advanced Trench Technology
- ◆ Surface mount package

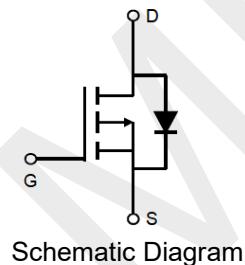
### 2. Applications

- ◆ Power Management
- ◆ Load Switching



SOT23-3  
Pin Description

V <sub>DS</sub>	R <sub>DS(on)</sub> Typ.	I <sub>D</sub>
-20V	15mΩ @ -4.5V	-6A
	19.5mΩ @ -2.5V	



Schematic Diagram

### 3. Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WX014P02S3	014P02	SOT23-3	3,000	180,000

### 4. Absolute Max Ratings at Ta=25°C (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V <sub>DSS</sub>	-20	V
Gate to Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (DC)	I <sub>D</sub>	-6	A
Drain Current (Pulse), PW≤300μs	I <sub>DP</sub>	-24	A
Total Dissipation	P <sub>D</sub>	1.3	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### 5. Thermal Resistance Ratings (Note 2)

Parameter	Symbol	Value	Unit
Junction to Ambient	R <sub>θJA</sub>	96	°C/W

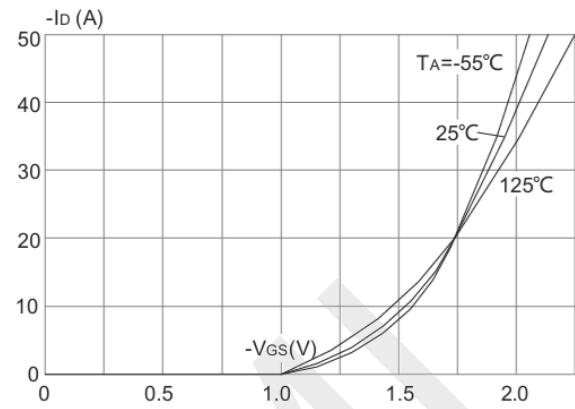
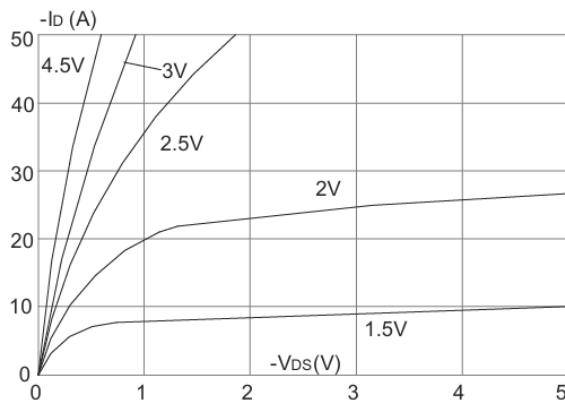
Note 2: When mounted on 1 inch square copper board t ≤ 10sec The value in any given application depends on the user's specific board design.

6.Electrical Characteristics at  $T_a=25^\circ C$  (Note 3)

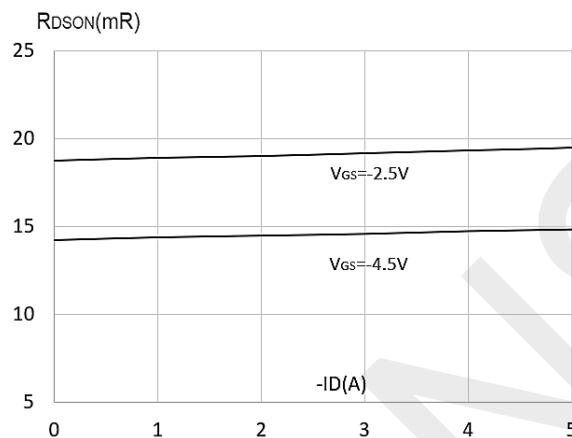
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -250\mu A, V_{GS} = 0V$	-20	-	-	V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -20V, V_{GS} = 0V$	-	-	-1	$\mu A$
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{DS}=-250\mu A$	-0.5	-0.7	-1.0	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = -6A, V_{GS} = -4.5V$	-	15	19	$m\Omega$
		$I_D = -5A, V_{GS} = -2.5V$	-	19.5	26	$m\Omega$
Input Capacitance	$C_{iss}$	$V_{GS}=0V,$ $V_{DS}=-10V,$ Frequency=1.0MHz	-	1846	-	pF
Output Capacitance	$C_{oss}$		-	192	-	pF
Reverse Transfer Capacitance	$C_{rss}$		-	175	-	pF
Turn-ON Delay Time	$t_{d(on)}$	$V_{DS} = -10V, I_D = -6A$ $V_{GS} = -4.5V, R_G = 2.4\Omega$	-	14	-	ns
Rise Time	$t_r$		-	79	-	ns
Turn-OFF Delay Time	$t_{d(off)}$		-	76	-	ns
Fall Time	$t_f$		-	76	-	ns
Total Gate Charge	$Q_g$	$V_{DS} = -10V,$ $V_{GS} = -4.5V,$ $I_D = -6A$	-	16	-	nC
	$Q_{gs}$		-	3	-	nC
	$Q_{gd}$		-	4	-	nC
Diode Forward Voltage	$V_{FSD}$	$I_S = -6A, V_{GS} = 0V$	-0.5	-	-1.2	V

Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

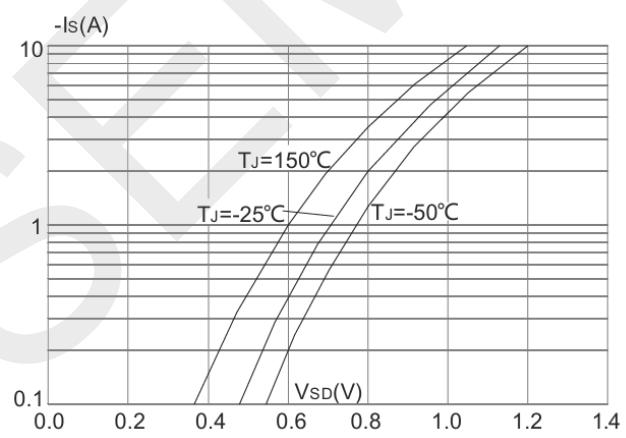
## 7.Typical Electrical and Thermal Characteristics



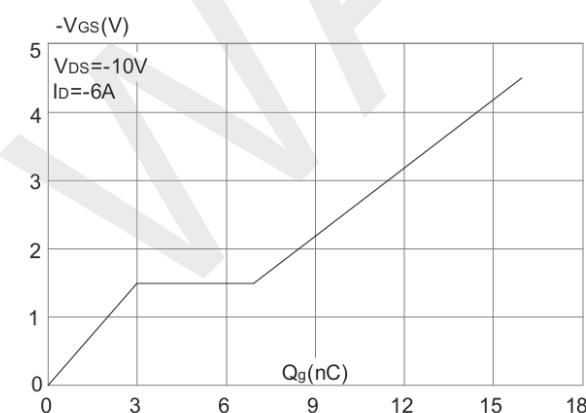
**Typical Output Characteristics**



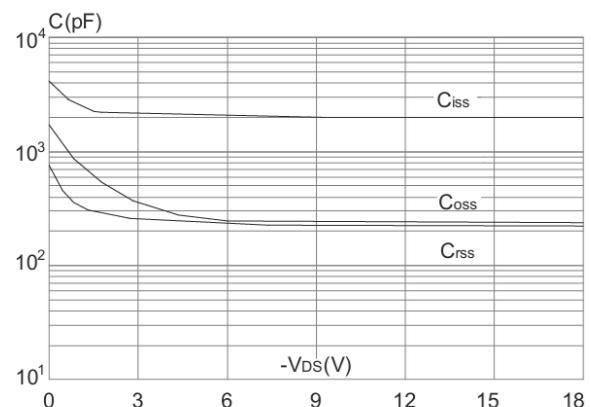
**Typical Transfer Characteristics**



**On-resistance vs. Drain Current**

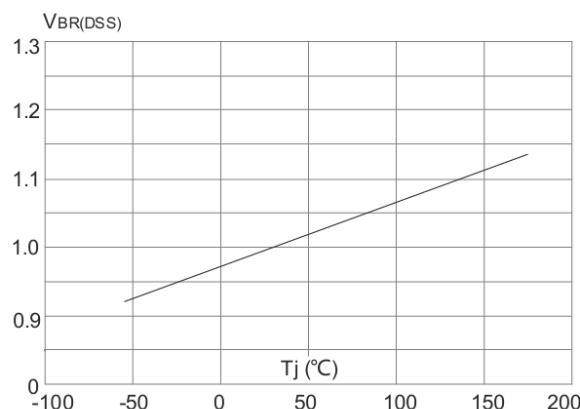


**Body Diode Characteristics**

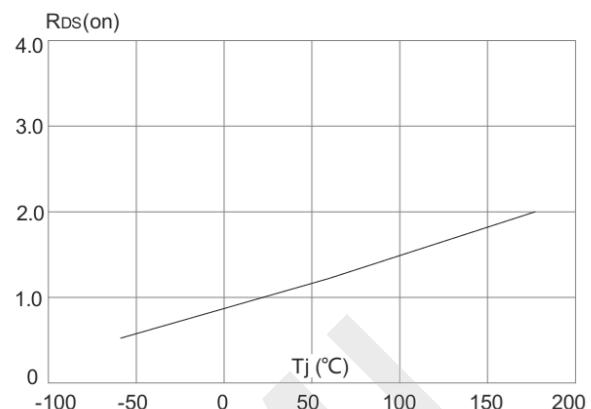


**Gate Charge Characteristics**

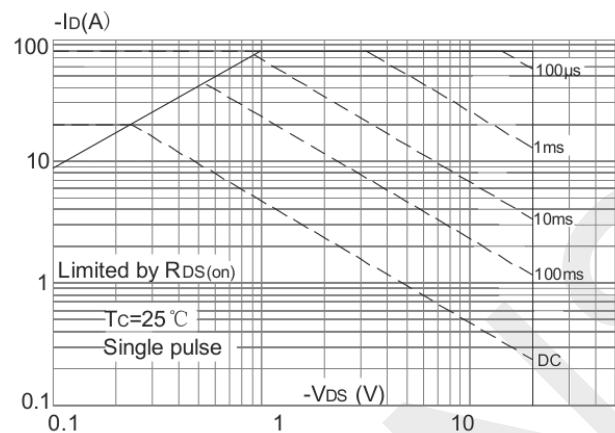
**Capacitance Characteristics**



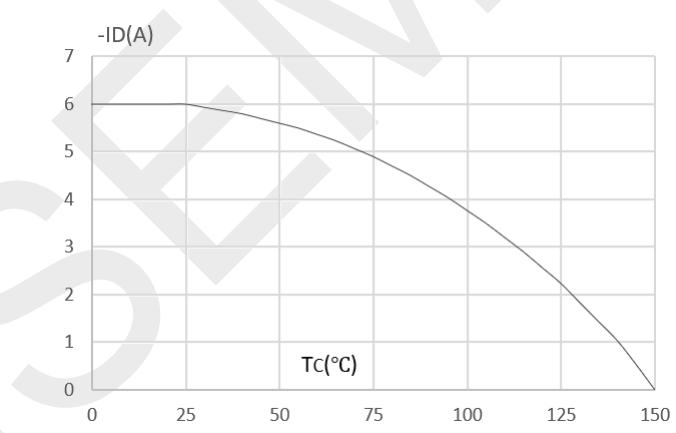
**Normalized Breakdown voltage vs.  
Junction Temperature**



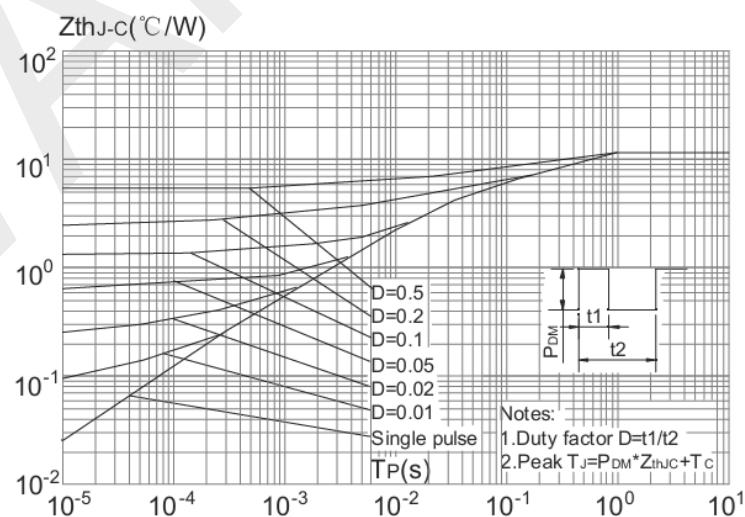
**Normalized on Resistance vs. Junction  
Temperature**



**Normalized Breakdown voltage vs.  
Junction Temperature**

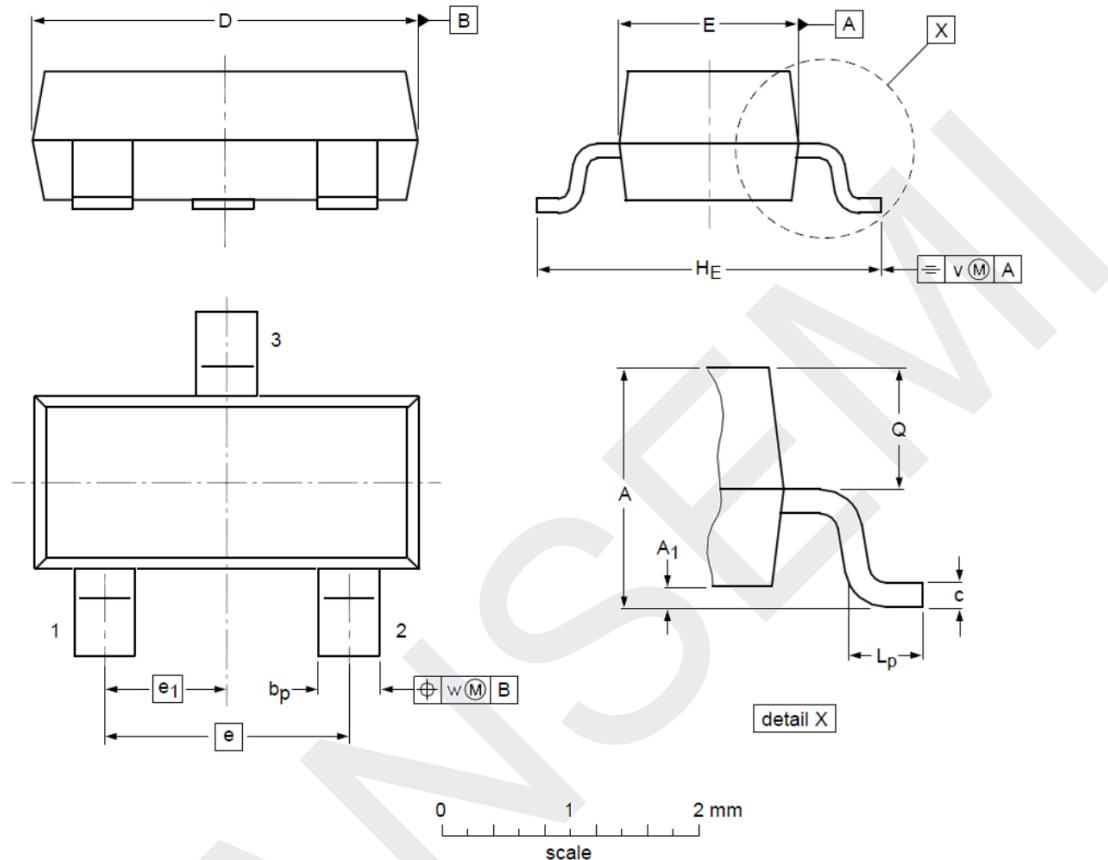


**Current De-rating**



**Normalized Maximum Transient Thermal Impedance**

## 8.Package Dimensions



DIMENSIONS ( unit : mm )

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
<b>A</b>	1.00	1.17	1.30	<b>A<sub>1</sub></b>	0.01	0.05	0.10
<b>b<sub>p</sub></b>	0.35	0.39	0.50	<b>c</b>	0.10	0.20	0.26
<b>D</b>	2.70	2.90	3.10	<b>E</b>	1.30	1.58	1.70
<b>e</b>	--	1.90	--	<b>e<sub>1</sub></b>	--	0.95	--
<b>H<sub>E</sub></b>	2.50	2.78	3.00	<b>L<sub>p</sub></b>	0.20	0.32	0.60
<b>Q</b>	0.23	0.27	0.33	<b>v</b>	--	0.20	--
<b>w</b>	--	0.20	--				

## 9.Important Notice

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